

19. The method of claim 18, further comprising:
selecting a number of active states of the write signal and of the read signal.
20. The method of claim 17, further comprising:
receiving a read command;
providing the row signal having the active state at the set time in response to receiving the write command;
providing a reading signal having at least a first active state, wherein the first active state occurs at the set delay after the active state of the row signal;
reading data from at least one memory cell in the opened row in response to the at least first active state of the read signal.
21. A random access memory (RAM) comprising:
means for providing a row signal having an active state in response to receiving a write command, wherein the active state occurs at a set time after receipt of the write command, and for providing a write signal having at least a first active state occurring at a set delay after the active state of the row signal;
and
an array of memory cells arranged in a plurality of rows and columns, wherein a selected row is opened for access in response to the active state of the row signal, and wherein data is written to at least one memory cell in the opened row in response to the at least first active state of the write signal.
22. The RAM of claim ²¹~~22~~, further comprising:
means for performing autonomous refresh operations of memory cells of the array within the set time and for providing a refresh signal having a first state when a refresh operation is in progress and a second state when a refresh operation is not in progress.
23. The RAM of claim 22, further comprising:

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